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FQD7P06 P-Channel QFET® MOSFET

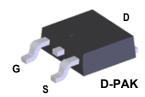
- 60 V, - 5.4 A, 450 m Ω

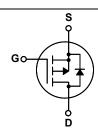
Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor® planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.



- - 5.4 A, 60 V, $R_{DS(on)}$ = 450 m Ω (Max.) @ V_{GS} = 10 V, I_D = 2.7 A
- Low Gate Charge (Typ. 6.3 nC)
- Low Crss (Typ. 25 pF)
- · 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter			FQD7P06	Unit
V _{DSS}	Drain-Source Voltage			-60	V
I _D	Drain Current	- Continuous (T _C = 25°C)		-5.4	A
		- Continuous (T _C = 100°C)		-3.42	Α
I _{DM}	Drain Current	- Pulsed	(Note 1)	-21.6	А
V _{GSS}	Gate-Source Vo	oltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	90	mJ
I _{AR}	Avalanche Current		(Note 1)	-5.4	Α
E _{AR}	Repetitive Avalanche Energy		(Note 1)	2.8	mJ
dv/dt	Peak Diode Red	k Diode Recovery dv/dt (Note 3)		-7.0	V/ns
P _D	Power Dissipation (T _A = 25°C) *		2.5	W	
	Power Dissipation (T _C = 25°C)			28	W
	- Derate above 25°C			0.22	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds			300	°C

Thermal Characteristics

Symbol	Parameter	FQD7P06	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	4.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	110	°C/W

^{*} When mounted on the minimum pad size recommended (PCB Mount)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-60			V
ΔBV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μA, Referenced to 25°C		-0.07		V/°C
I _{DSS}	7 0 1 1/1 1 1 1 1 1	V _{DS} = -60 V, V _{GS} = 0 V			-1	μА
	Zero Gate Voltage Drain Current	V _{DS} = -48 V, T _C = 125°C			-10	μА
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse V _{GS} = 25 V, V _{DS} = 0 V				100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250 μA	-2.0		-4.0	V
R _{DS(on)}	Static Drain-Source $V_{GS} = -10 \text{ V}, I_D = -2.7 \text{ A}$		-	0.36	0.451	Ω
9 _{FS}	Forward Transconductance $V_{DS} = -30 \text{ V}, I_D = -2.7 \text{ A}$			3.8		S
Dynam	ic Characteristics					
C _{iss}	Input Capacitance	V _{DS} = -25 V, V _{GS} = 0 V, f = 1.0 MHz		225	295	pF
C _{oss}	Output Capacitance			110	145	pF
C _{rss}	Reverse Transfer Capacitance			25	32	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	On Delay Time $V_{DD} = -30 \text{ V}, I_D = -3.5 \text{ A},$		7	25	ns
t _r	Turn-On Rise Time			50	110	ns
t _{d(off)}	Turn-Off Delay Time	$R_G = 25 \Omega$		7.5	25	ns
t _f	Turn-Off Fall Time	(Note 4)		25	60	ns
Qg	Total Gate Charge	V _{DS} = -48 V, I _D = -7.0 A,		6.3	8.2	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V		1.6		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		3.1		nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Did	ode Forward Current			-5.4	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	orward Current			-21.6	Α
V _{SD}	Drain-Source Diode Forward Voltage	ard Voltage $V_{GS} = 0 \text{ V}, I_S = -5.4 \text{ A}$			-4.0	V
t _{rr}	Reverse Recovery Time $V_{GS} = 0 \text{ V, I}_{S} = -7.0 \text{ A},$			77		ns
Q _{rr}	Reverse Recovery Charge dl _F / dt = 100 A/μs			0.23		μС

Notes: 1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 3.6mH, I $_{AS}$ = -5.4A, V $_{DD}$ = -25V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C 3. $_{SD}$ \leq -7.0A, di/dt \leq 300A/ $_{J}$ s, V $_{DD}$ \leq BV $_{DSS}$, Starting T $_{J}$ = 25°C 4. Essentially independent of operating temperature

Typical Characteristics

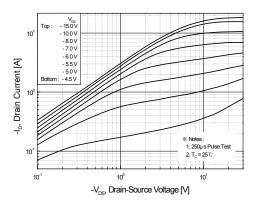


Figure 1. On-Region Characteristics

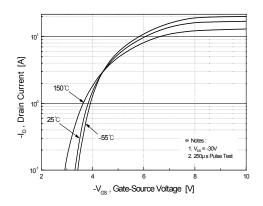


Figure 2. Transfer Characteristics

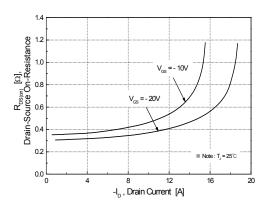


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

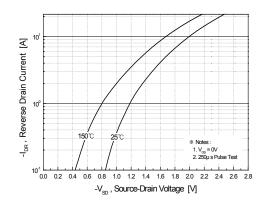


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

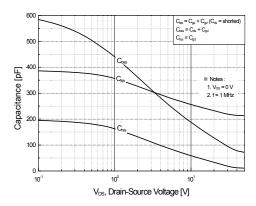


Figure 5. Capacitance Characteristics

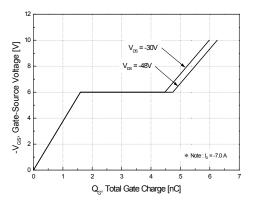


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

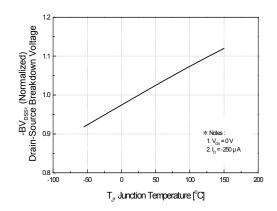
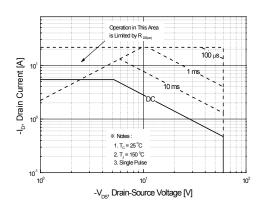


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



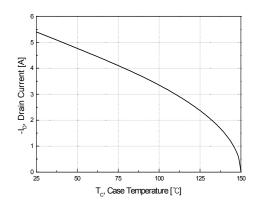


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

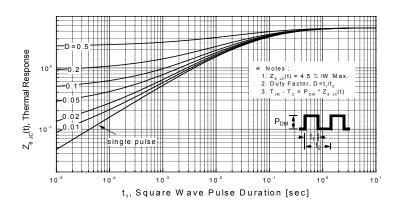
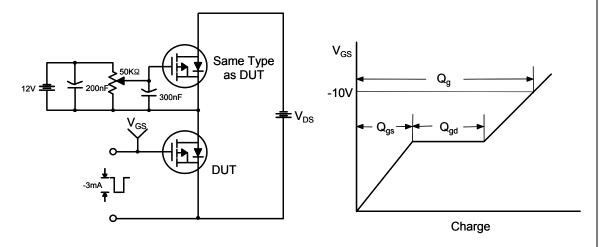
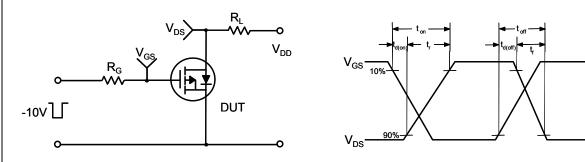


Figure 11. Transient Thermal Response Curve

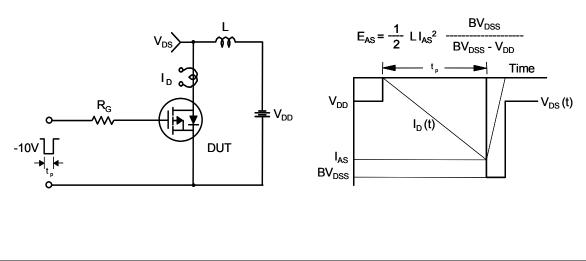
Gate Charge Test Circuit & Waveform



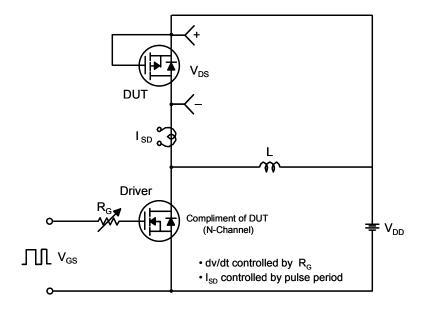
Resistive Switching Test Circuit & Waveforms

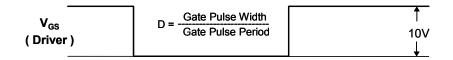


Unclamped Inductive Switching Test Circuit & Waveforms

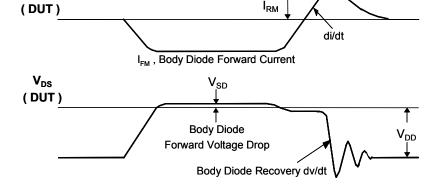


Peak Diode Recovery dv/dt Test Circuit & Waveforms





Body Diode Reverse Current



I_{SD}

Package Dimensions DPAK A -6.00 MIN - 6.50 MIN 6.22 5.97 _1.02 MAX 6.25 c 3.00 MIN (0.59)0.89 1.40 MIN 2.30 2.29 ⊕ 0.25**M** A**M** C 4.60 LAND PATTERN RECOMMENDATION SEE 4.32 MIN NOTE D 5.21 MIN 10.41 9.40 SEE DETAIL A □ 0.10 B NOTES: UNLESS OTHERWISE SPECIFIED A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA. B) ALL DIMENSIONS ARE IN MILLIMETERS. C) DIMENSIONING AND TOLENALCING PER ASME Y14.5M-1994. D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION. E) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL. E) DIMENSIONS ARE EXCLUSSIVE OF BURSS. 0.51 GAGE PLANE 10. (1.54)1.78 1.40 0.127 MAX IS OPTIONAL. DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS. LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD T0220P1003X238-3N. DRAWING NUMBER AND REVISION: MKT-T0252A03REV8 F) SEATING PLANE -(2.90)G) DETAIL A (ROTATED -90°) SCALE: 12X





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